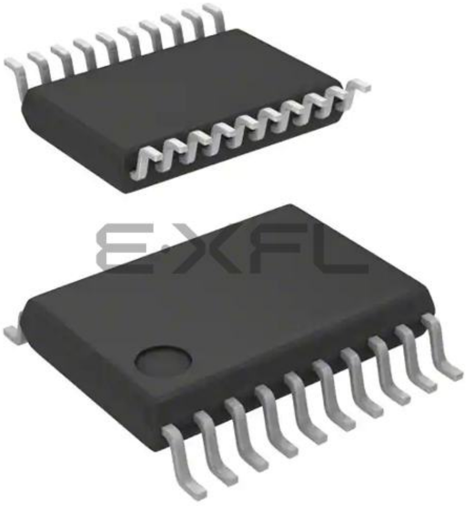

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	SIO, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	13
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21182dsp-u0

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R8C/18 Group, R8C/19 Group

SINGLE-CHIP 16-BIT CMOS MCU

REJ03B0124-0140
Rev.1.40
Apr 14, 2006

1. Overview

These MCUs are fabricated using a high-performance silicon gate CMOS process, embedding the R8C/Tiny Series CPU core, and is packaged in a 20-pin molded-plastic LSSOP, SDIP or a 28-pin plastic molded-HWQFN. It implements sophisticated instructions for a high level of instruction efficiency. With 1 Mbyte of address space, they are capable of executing instructions at high speed.
Furthermore, the R8C/19 Group has on-chip data flash ROM (1 KB × 2 blocks).
The difference between the R8C/18 Group and R8C/19 Group is only the presence or absence of data flash ROM. Their peripheral functions are the same.

1.1 Applications

Electric household appliances, office equipment, housing equipment (sensors, security systems), general industrial equipment, audio equipment, etc.

1.2 Performance Overview

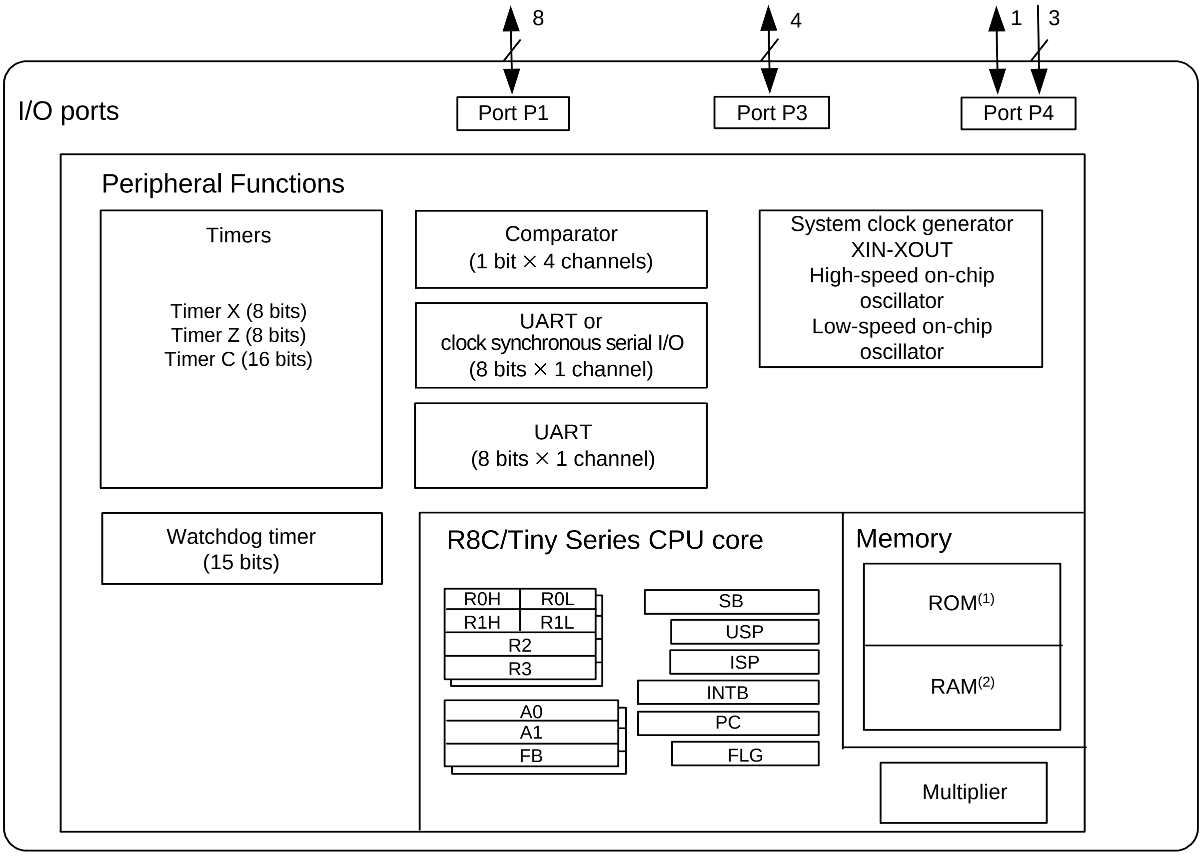
Table 1.1 outlines the Functions and Specifications for R8C/18 Group and Table 1.2 outlines the Functions and Specifications for R8C/19 Group.

Table 1.1 Functions and Specifications for R8C/18 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operation mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.3 Product Information for R8C/18 Group**
Peripheral Functions	Ports	I/O ports: 13 pins (including LED drive port) Input port: 3 pins
	LED drive ports	I/O ports: 4 pins
	Timers	Timer X: 8 bits × 1 channel, timer Z: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer C: 16 bits × 1 channel (Input capture and output compare circuits)
	Serial interfaces	1 channel Clock synchronous serial I/O, UART 1 channel UART
	Comparator	1-bit comparator: 1 circuit, 4 channels
	Watchdog timer	15 bits × 1 channel (with prescaler) Reset start selectable, count source protection mode
	Interrupts	Internal: 10 sources, External: 4 sources, Software: 4 sources, Priority levels: 7 levels
	Clock generation circuits	2 circuits • Main clock oscillation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has frequency adjustment function
	Oscillation stop detection function	Main clock oscillation stop detection function
	Voltage detection circuit	On-chip
	Power-on reset circuit	On-chip
Electric Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
	Current consumption	Typ. 9 mA (VCC = 5.0 V, f(XIN) = 20 MHz, comparator stopped) Typ. 5 mA (VCC = 3.0V, f(XIN) = 10 MHz, comparator stopped) Typ. 35 µA (VCC = 3.0 V, wait mode, peripheral clock off) Typ. 0.7 µA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	100 times
Operating Ambient Temperature		-20 to 85°C -40 to 85°C (D version)
Package		20-pin molded-plastic LSSOP
		20-pin molded-plastic SDIP
		28-pin molded-plastic HWQFN

1.3 Block Diagram

Figure 1.1 shows a Block Diagram.



NOTES:
1. ROM size varies with MCU type.
2. RAM size varies with MCU type.

Figure 1.1 Block Diagram

1.4 Product Information

Table 1.3 lists Product Information for R8C/18 Group and Table 1.4 lists Product Information for R8C/19 Group.

Table 1.3 Product Information for R8C/18 Group **Current of Apr. 2006**

Type No.	ROM Capacity	RAM Capacity	Package Type	Remarks
R5F21181SP	4 Kbytes	384 bytes	PLSP0020JB-A	Flash memory version
R5F21182SP	8 Kbytes	512 bytes	PLSP0020JB-A	
R5F21183SP	12 Kbytes	768 bytes	PLSP0020JB-A	
R5F21184SP	16 Kbytes	1 Kbyte	PLSP0020JB-A	
R5F21181DSP (D)	4 Kbytes	384 bytes	PLSP0020JB-A	D version
R5F21182DSP (D)	8 Kbytes	512 bytes	PLSP0020JB-A	
R5F21183DSP (D)	12 Kbytes	768 bytes	PLSP0020JB-A	
R5F21184DSP (D)	16 Kbytes	1 Kbyte	PLSP0020JB-A	
R5F21181DD	4 Kbytes	384 bytes	PRDP0020BA-A	Flash memory version
R5F21182DD	8 Kbytes	512 bytes	PRDP0020BA-A	
R5F21183DD	12 Kbytes	768 bytes	PRDP0020BA-A	
R5F21184DD	16 Kbytes	1 Kbyte	PRDP0020BA-A	
R5F21182NP	8 Kbytes	512 bytes	PWQN0028KA-B	Flash memory version
R5F21183NP	12 Kbytes	768 bytes	PWQN0028KA-B	
R5F21184NP	16 Kbytes	1 Kbyte	PWQN0028KA-B	

(D): Under Development

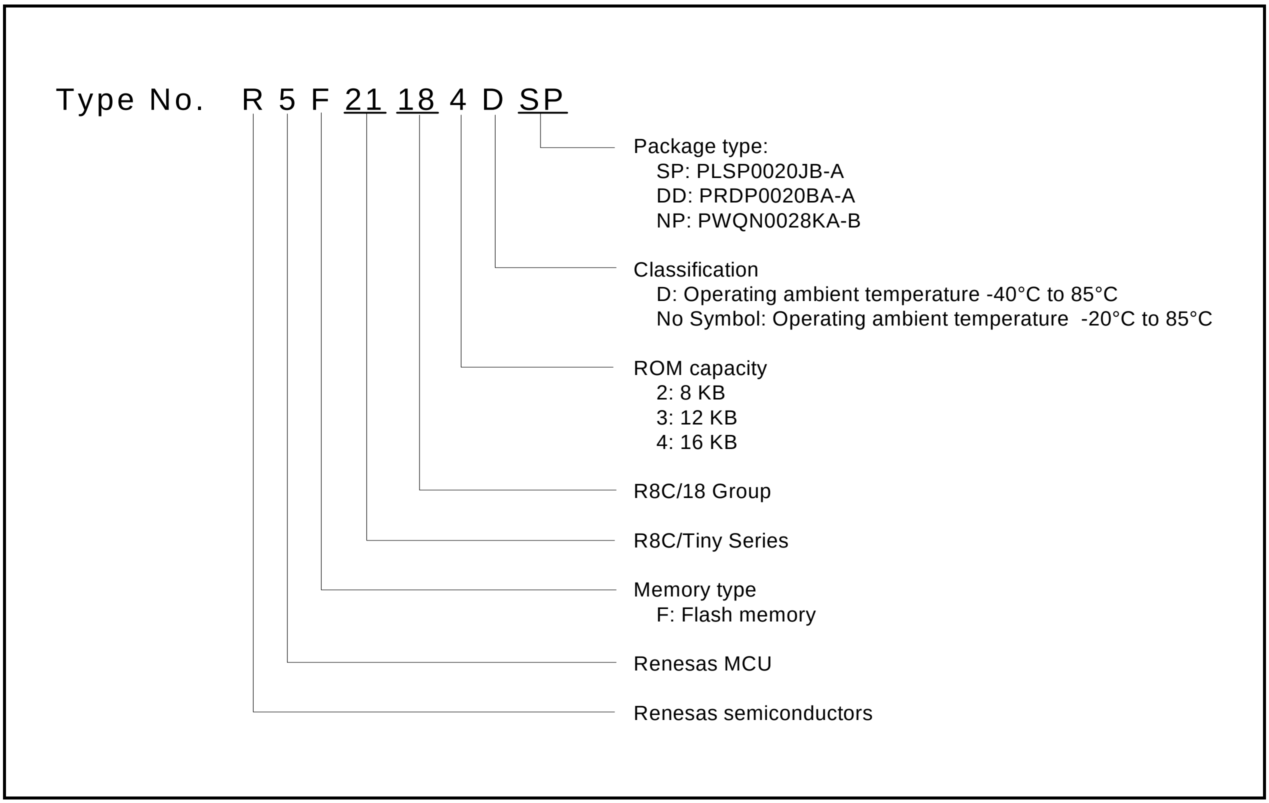
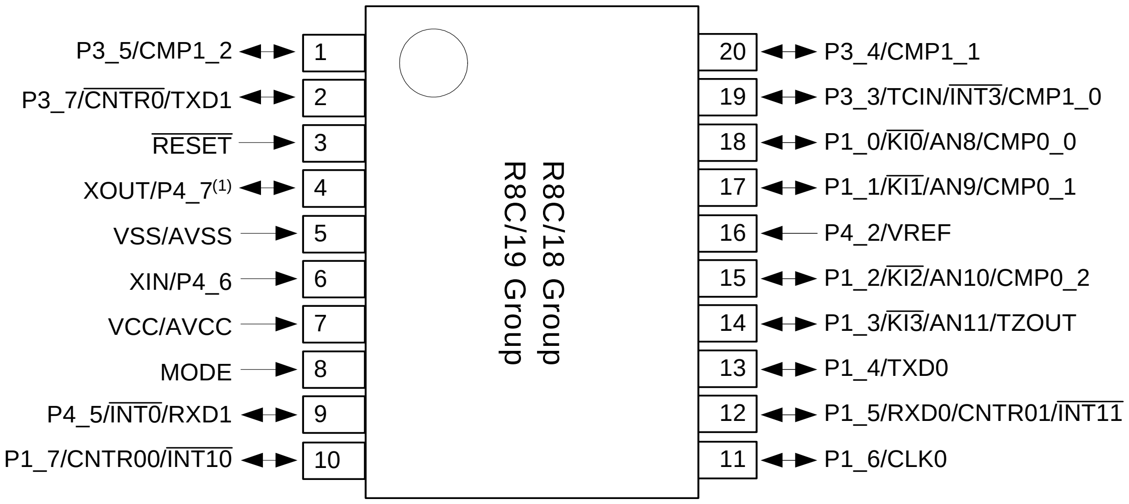


Figure 1.2 Type Number, Memory Size, and Package of R8C/18 Group

1.5 Pin Assignments

Figure 1.4 shows Pin Assignments for PLSP0020JB-A Package (Top View), Figure 1.5 shows Pin Assignments for PRDP0020BA-A Package (Top View) and Figure 1.6 shows Pin Assignments for PWQN0028KA-B Package (Top View).

PIN assignments (top view)



NOTE:
1. P4_7 is an input-only port.

Package: PLSP0020JB-A(20P2F-A)

Figure 1.4 Pin Assignments for PLSP0020JB-A Package (Top View)

Table 1.6 Pin Name Information by Pin Number of PLSP0020JB-A, PRDP0020BA-A packages

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules			
			Interrupt	Timer	Serial Interface	Comparator
1		P3_5		CMP1_2		
2		P3_7		$\overline{\text{CNTR0}}$	TXD1	
3	$\overline{\text{RESET}}$					
4	XOUT	P4_7				
5	VSS/AVSS					
6	XIN	P4_6				
7	VCC/AVCC					
8	MODE					
9		P4_5	$\overline{\text{INT0}}$		RXD1	
10		P1_7	$\overline{\text{INT10}}$	CNTR00		
11		P1_6			CLK0	
12		P1_5	$\overline{\text{INT11}}$	CNTR01	RXD0	
13		P1_4			TXD0	
14		P1_3	$\overline{\text{KI3}}$	TZOUT		AN11
15		P1_2	$\overline{\text{KI2}}$	CMP0_2		AN10
16	VREF	P4_2				
17		P1_1	$\overline{\text{KI1}}$	CMP0_1		AN9
18		P1_0	$\overline{\text{KI0}}$	CMP0_0		AN8
19		P3_3	$\overline{\text{INT3}}$	TCIN/CMP1_0		
20		P3_4		CMP1_1		

Table 4.3 SFR Information (3)(1)

Address	Register	Symbol	After reset
0080h	Timer Z Mode Register	TZMR	00h
0081h			
0082h			
0083h			
0084h	Timer Z Waveform Output Control Register	PUM	00h
0085h	Prescaler Z Register	PREZ	FFh
0086h	Timer Z Secondary Register	TZSC	FFh
0087h	Timer Z Primary Register	TZPR	FFh
0088h			
0089h			
008Ah	Timer Z Output Control Register	TZOC	00h
008Bh	Timer X Mode Register	TXMR	00h
008Ch	Prescaler X Register	PREX	FFh
008Dh	Timer X Register	TX	FFh
008Eh	Timer Count Source Setting Register	TCSS	00h
008Fh			
0090h	Timer C Register	TC	00h
0091h			00h
0092h			
0093h			
0094h			
0095h			
0096h	External Input Enable Register	INTEN	00h
0097h			
0098h	Key Input Enable Register	KIEN	00h
0099h			
009Ah	Timer C Control Register 0	TCC0	00h
009Bh	Timer C Control Register 1	TCC1	00h
009Ch	Capture, Compare 0 Register	TM0	00h
009Dh			00h(2)
009Eh	Compare 1 Register	TM1	FFh
009Fh			FFh
00A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit/Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h	UART1 Transmit/Receive Mode Register	U1MR	00h
00A9h	UART1 Bit Rate Register	U1BRG	XXh
00AAh	UART1 Transmit Buffer Register	U1TB	XXh
00ABh			XXh
00ACh	UART1 Transmit/Receive Control Register 0	U1C0	00001000b
00ADh	UART1 Transmit/Receive Control Register 1	U1C1	00000010b
00AEh	UART1 Receive Buffer Register	U1RB	XXh
00AFh			XXh
00B0h	UART Transmit/Receive Control Register 2	UCON	00h
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h			
00B9h			
00BAh			
00BBh			
00BCh			
00BDh			
00BEh			
00BFh			

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. When the output compare mode is selected (the TCC13 bit in the TCC1 register = 1), the value is set to $FFFF_{16}$.

Table 5.3 Comparator Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Resolution		–	–	1	Bit
–	Absolute accuracy	ϕ_{AD} = 10 MHz(3)	–	–	±20	mV
t_{conv}	Conversion time	ϕ_{AD} = 10 MHz(3)	1	–	–	µs
V_{ref}	Reference voltage		0	–	AV_{CC}	V
V_{IA}	Analog input voltage		0	–	AV_{CC}	V
–	Comparator conversion operating clock frequency(2)		1	–	10	MHz

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. If f1 exceeds 10 MHz, divided f1 and ensure the comparator conversion operating clock frequency (ϕ_{AD}) is 10 MHz or below.
3. If AVcc is less than 4.2 V, divided f1 and ensure the comparator conversion operating clock frequency (ϕ_{AD}) is f1/2 or below.

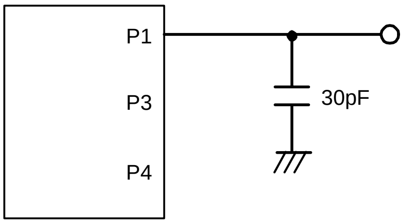


Figure 5.1 Port P1, P3, and P4 Measurement Circuit

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/18 Group	100(3)	–	–	times
		R8C/19 Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	μs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	μs
–	Interval from erase start/restart until following suspend request		650	–	–	μs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	μs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(8)	Ambient temperature = 55 °C	20	–	–	year

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to Suspend can be applied to the request.However, we recommend that a suspend request with an interval of less than 650 μs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the number of erase operations between block A and block B can further reduce the effective number of rewrites. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance[2]		10,000[3]	–	–	times
–	Byte program time (Program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (Program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (Program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (Program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		-20[8]	–	85	°C
–	Data hold time[9]	Ambient temperature = 55 °C	20	–	–	year

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to suspend can be applied to the request. However, we recommend that a suspend request with an interval of less than 650 µs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. -40 °C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

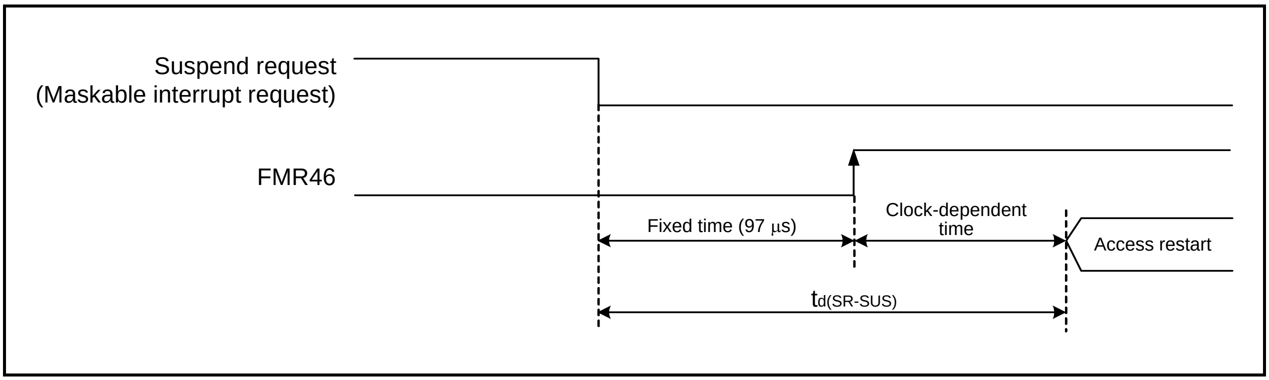


Figure 5.2 Transition Time to Suspend

Table 5.6 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(3)		2.70	2.85	3.00	V
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	600	–	nA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	100	µs
Vccmin	MCU operating voltage minimum value		2.7	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
3. Ensure that $V_{det2} > V_{det1}$.

Table 5.7 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level(4)		3.00	3.30	3.60	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	600	–	nA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
4. Ensure that $V_{det2} > V_{det1}$.

Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	High-speed on-chip oscillator frequency when the reset is deasserted	V_{CC} = 5.0 V, T_{opr} = 25 °C	–	8	–	MHz
–	High-speed on-chip oscillator frequency temperature supply voltage dependence[2]	0 to +60 °C/5 V ± 5 %[3]	7.76	–	8.24	MHz
		-20 to +85 °C/2.7 to 5.5 V[3]	7.68	–	8.32	MHz
		-40 to +85 °C/2.7 to 5.5 V[3]	7.44	–	8.32	MHz

NOTES:
1. The measurement condition is V_{CC} = 5.0 V and T_{opr} = 25 °C.
2. Refer to **10.6.4 High-Speed On-Chip Oscillator Clock** for notes on high-speed on-chip oscillator clock.
3. The standard value shows when the HRA1 register is assumed as the value in shipping and the HRA2 register value is set to 00h.

Table 5.11 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on[2]		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time[3]		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and T_{opr} = 25 °C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until CPU clock supply starts after the interrupt is acknowledged to exit stop mode.

Table 5.17 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	–	ns
$t_{W(CKH)}$	CLKi input “H” width	100	–	ns
$t_{W(CKL)}$	CLKi input “L” width	100	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	50	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 1

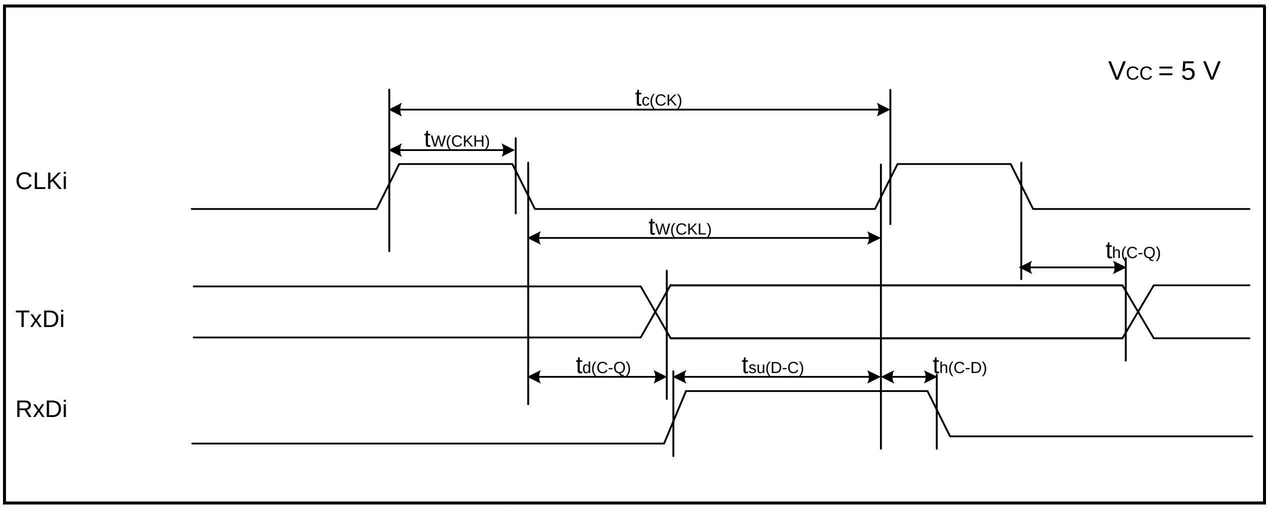


Figure 5.7 Serial Interface Timing Diagram when V_{CC} = 5 V

Table 5.18 External Interrupt $\overline{\text{INT0}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{\text{INT0}}$ input “H” width	250[1]	–	ns
$t_{W(INL)}$	$\overline{\text{INT0}}$ input “L” width	250[2]	–	ns

NOTES:

1. When selecting the digital filter by the $\overline{\text{INT0}}$ input filter select bit, use an $\overline{\text{INT0}}$ input HIGH width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{\text{INT0}}$ input filter select bit, use an $\overline{\text{INT0}}$ input LOW width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.

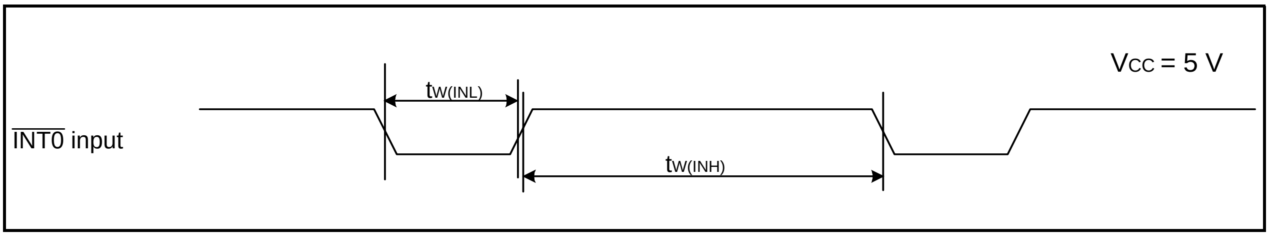


Figure 5.8 External Interrupt $\overline{\text{INT0}}$ Input Timing Diagram when V_{CC} = 5 V

Timing requirements
(Unless Otherwise Specified: V_{CC} = 3 V, V_{SS} = 0 V at Ta = 25 °C) [V_{CC} = 3 V]

Table 5.21 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	100	–	ns
$t_{WH(XIN)}$	XIN input “H” width	40	–	ns
$t_{WL(XIN)}$	XIN input “L” width	40	–	ns

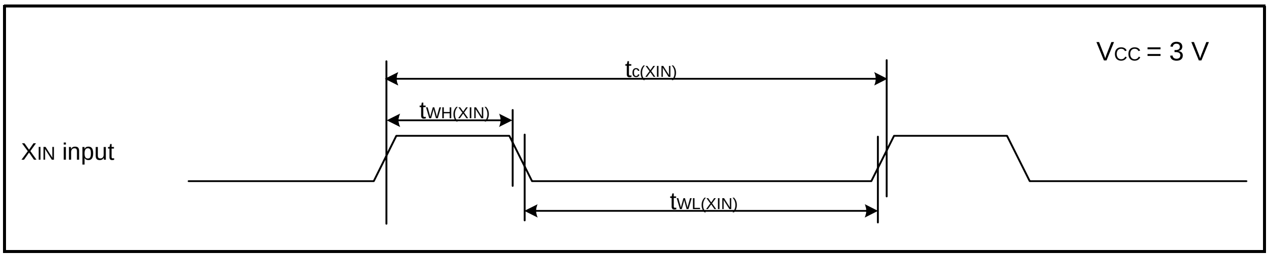


Figure 5.9 XIN Input Timing Diagram when V_{CC} = 3 V

Table 5.22 CNTR0 Input, CNTR1 Input, $\overline{\text{INT1}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CNTR0)}$	CNTR0 input cycle time	300	–	ns
$t_{WH(CNTR0)}$	CNTR0 input “H” width	120	–	ns
$t_{WL(CNTR0)}$	CNTR0 input “L” width	120	–	ns

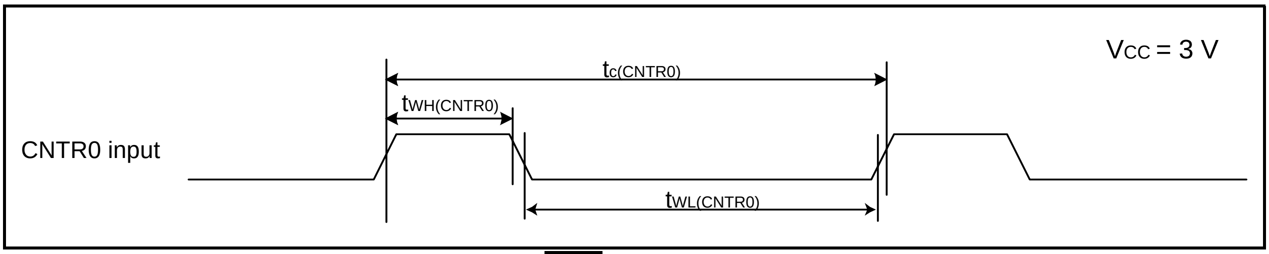


Figure 5.10 CNTR0 Input, CNTR1 Input, $\overline{\text{INT1}}$ Input Timing Diagram when V_{CC} = 3 V

Table 5.23 TCIN Input, $\overline{\text{INT3}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TCIN)}$	TCIN input cycle time	1,200(1)	–	ns
$t_{WH(TCIN)}$	TCIN input “H” width	600(2)	–	ns
$t_{WL(TCIN)}$	TCIN input “L” width	600(2)	–	ns

NOTES:
1. When using the timer C input capture mode, adjust the cycle time to (1/timer C count source frequency × 3) or above.
2. When using the timer C input capture mode, adjust the width to (1/timer C count source frequency × 1.5) or above.

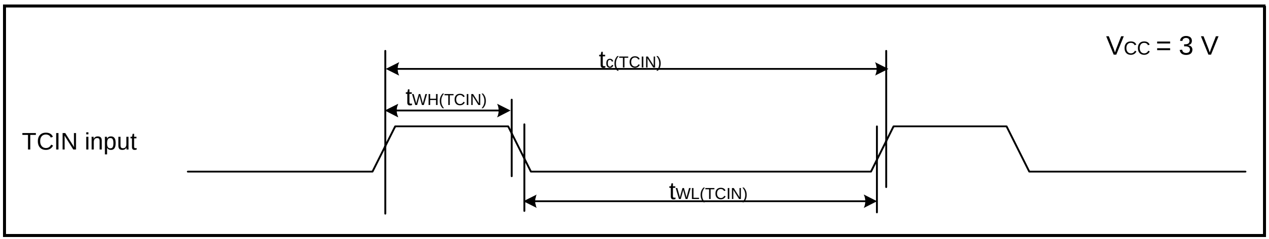


Figure 5.11 TCIN Input, $\overline{\text{INT3}}$ Input Timing Diagram when V_{CC} = 3 V

Table 5.24 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300	–	ns
$t_{W(CKH)}$	CLKi input "H" width	150	–	ns
$t_{W(CKL)}$	CLKi input "L" width	150	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	70	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 1

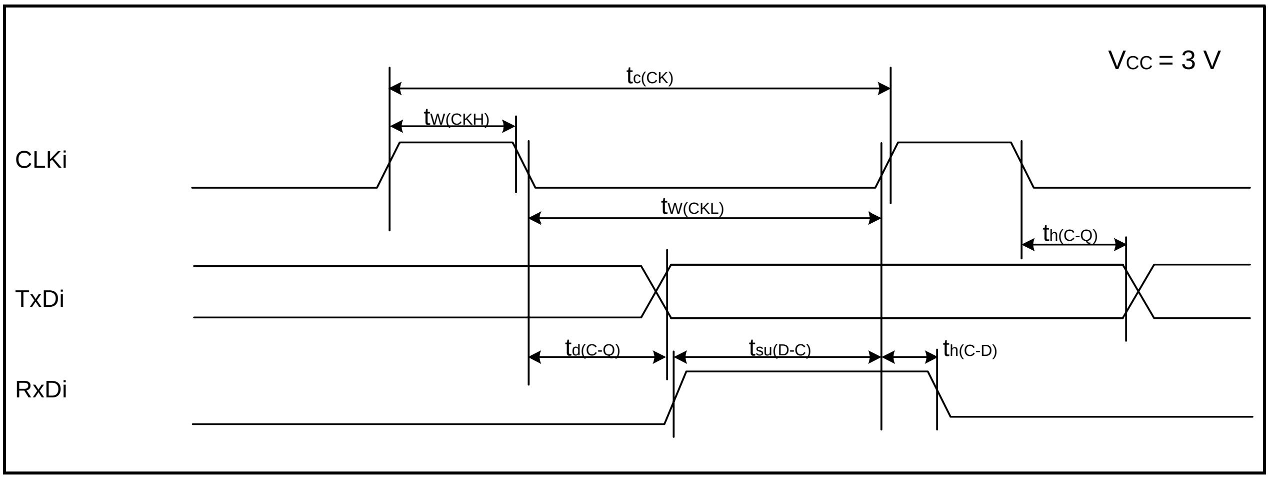


Figure 5.12 Serial Interface Timing Diagram when V_{CC} = 3 V

Table 5.25 External Interrupt $\overline{\text{INT0}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{\text{INT0}}$ input "H" width	380(1)	–	ns
$t_{W(INL)}$	$\overline{\text{INT0}}$ input "L" width	380(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{\text{INT0}}$ input filter select bit, use an $\overline{\text{INT0}}$ input HIGH width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{\text{INT0}}$ input filter select bit, use an $\overline{\text{INT0}}$ input LOW width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.

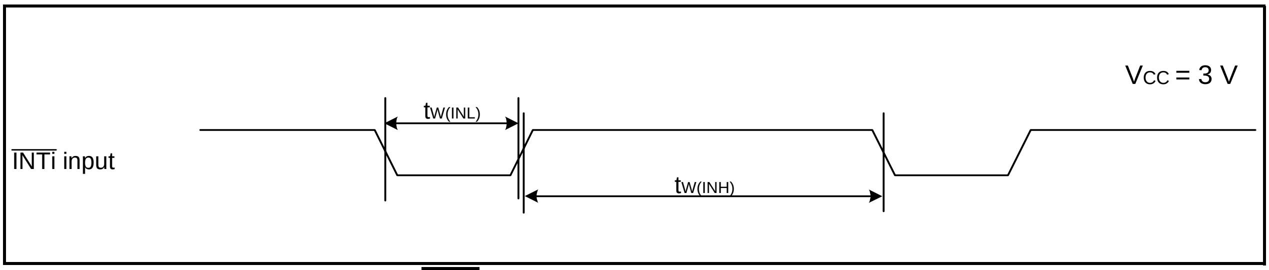
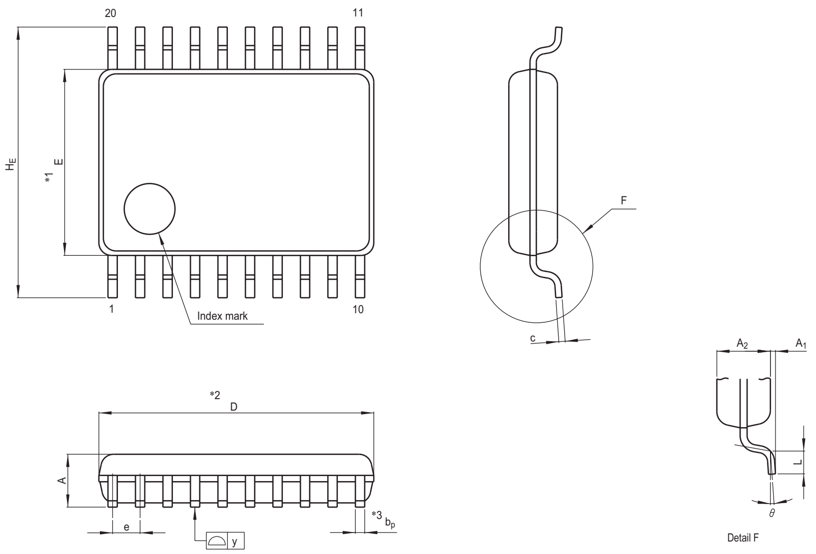


Figure 5.13 External Interrupt $\overline{\text{INT0}}$ Input Timing Diagram when V_{CC} = 3 V

Package Dimensions

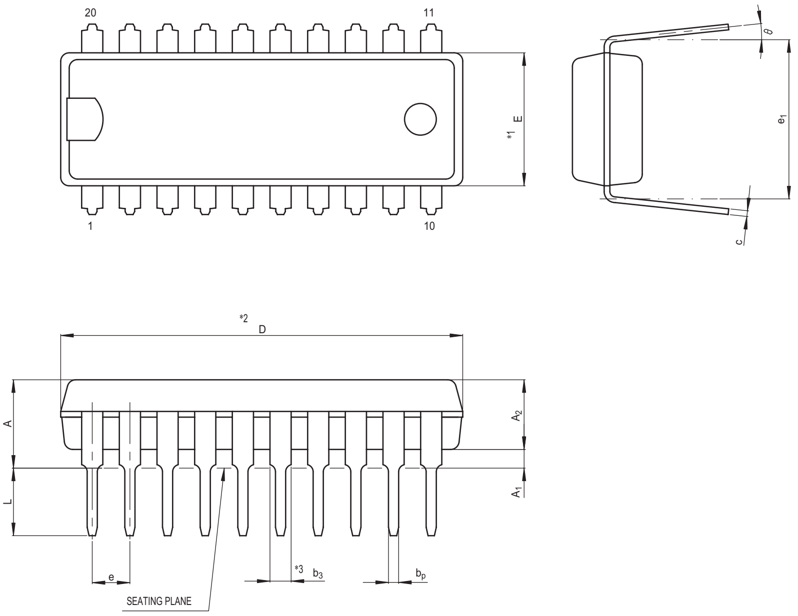
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	20P2F-A	0.1g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.4	6.5	6.6
E	4.3	4.4	4.5
A_2	—	1.15	—
A	—	—	1.45
A_1	0	0.1	0.2
b_p	0.17	0.22	0.32
c	0.13	0.15	0.2
θ	0°	—	10°
H_E	6.2	6.4	6.6
e	0.53	0.65	0.77
y	—	—	0.10
L	0.3	0.5	0.7

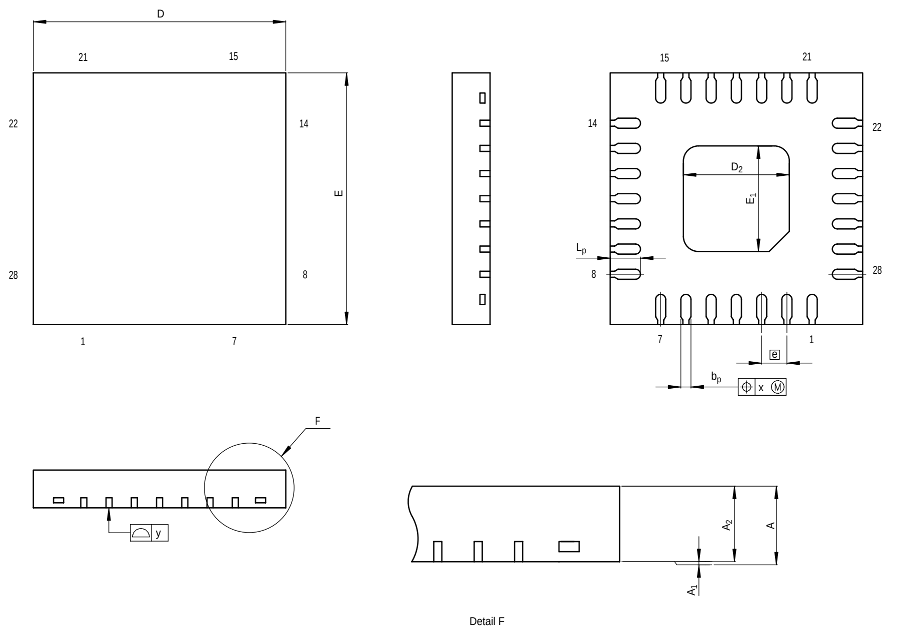
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-SDIP20-6.3x19-1.78	PRDP0020BA-A	20P4B	1.0g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
e_1	7.32	7.62	7.92
D	18.8	19.0	19.2
E	6.15	6.3	6.45
A	—	—	4.5
A_1	0.51	—	—
A_2	—	3.3	—
b_p	0.38	0.48	0.58
b_3	0.9	1.0	1.3
c	0.22	0.27	0.34
θ	0°	—	15°
e	1.528	1.778	2.028
L	3.0	—	—

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-HWQFN28-5x5-0.50	PWQN0028KA-B	28PJW-B	0.05g



Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	4.9	5.0	5.1
E	4.9	5.0	5.1
A_2	—	0.75	—
A	—	—	0.8
A_1	0	0	0.05
b_p	0.15	0.2	0.25
e	—	0.5	—
L_p	0.5	0.6	0.7
x	—	—	0.05
y	—	—	0.05
D_2	—	—	2.0
E_1	—	—	2.0

REVISION HISTORY	R8C/18 Group, R8C/19 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Nov 15, 2004	–	First Edition issued
0.20	Jan 11, 2005	5, 6	Tables 1.3 and 1.4: The date updated
0.21	Apr 04, 2005	2, 3	Tables 1.1 and 1.2: Partly revised
		4	Figure 1.1: Partly revised
		5, 6	Tables 1.3 and 1.4: Partly revised
		5, 6	Figure 1.2 and 1.3: Partly revised
		7, 8	Figure 1.4 and 1.5: Partly revised
		10	Table 1.6: Partly revised
		16	Table 4.1: Partly revised
		17	Table 4.2: Partly revised
		18	Table 4.3: Partly revised
		20	Package Dimensions are revised
1.00	May 27, 2005	5, 6	Tables 1.3 and 1.4: Partly revised
		9	Table 1.5: Partly revised
		25	Table 5.9: Revised
		26	Table 5.10: Partly revised
		28	Table 5.13: Partly revised
		32	Table 5.20: Partly revised
1.10	Jun 09, 2005	26	Table 5.10: Partly revised
1.20	Nov 01, 2005	3	Table 1.2 Performance Outline of the R8C/19 Group; Flash Memory: (Data area) → (Data flash) (Program area) → (Program ROM) revised
		4	Figure 1.1 Block Diagram; “Peripheral Function” added, “System Clock Generation” → “System Clock Generator” revised
		6	Table 1.4 Product Information of R8C/19 Group; ROM capacity: “Program area” → “Program ROM”, “Data area” → “Data flash” revised
		9	Table 1.5 Pin Description; Power Supply Input: “VCC/AVCC” → “VCC”, “VSS/AVSS” → “VSS” revised Analog Power Supply Input: added
		11	Figure 2.1 CPU Register; “Reserved Area” → “Reserved Bit” revised
		13	2.8.10 Reserved Area; “Reserved Area” → “Reserved Bit” revised
		15	3.2 R8C/19 Group, Figure 3.2 Memory Map of R8C/19 Group; “Data area” → “Data flash”, “Program area” → “Program ROM” revised

REVISION HISTORY | R8C/18 Group, R8C/19 Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.20	Nov 01, 2005	16	Table 4.1 SFR Information(1); 0009h: “XXXXXX00b” → “00h” 000Ah: “00XXX000b” → “00h” 001Eh: “XXXXX000b” → “00h” revised
		18	Table 4.3 SFR Information(3); 0085h: “Prescaler Z” → “Prescaler Z Register” 0086h: “Timer Z Secondary” → “Timer Z Secondary Register” 0087h: “Timer Z Primary” → “Timer Z Primary Register” 008Ch: “Prescaler X” → “Prescaler X Register” 008Dh: “Timer X” → “Timer X Register” 0090h, 0091h: “Timer C” → “Timer C Register” revised
		22	Table 5.4 Flash Memory (Program ROM) Electrical Characteristics; NOTES 3 and 5 revised, NOTE8 deleted
		23	Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics; NOTES 1 and 3 revised
		25	Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset); NOTE 2 revised
		26	Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics; “High-Speed On-Chip Oscillator ...” → “High-Speed On-Chip Oscillator Frequency ...” revised NOTE 2, 3 added
		28	Table 5.13 Electrical Characteristics (2) [Vcc = 5V]; NOTE 1 deleted
		32	Table 5.20 Electrical Characteristics (4) [Vcc = 3V]; NOTE 1 deleted
1.30	Dec 16, 2005	–	Products of PWQN0028KA-B package included
		5, 6	Table 1.3, Table 1.4 revised
		24	Table 5.4 Flash Memory (Program ROM) Electrical Characteristics; Ta → Ambient temperature
		25	Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics; Ta → Ambient temperature
		30, 34	Table 5.13, Table 5.20; The title revised, Condition of Stop Mode added
		32, 36	Table 5.17, Table 5.24; td(C-Q) and tsu(D-C) revised
		37, 38	Package Dimensions revised
1.40	Apr 14, 2006	2, 3	Table 1.1, Table 1.2; Interrupts: Internal 8 → 10 sources,
		5, 6	Table 1.3, Table 1.4; Type No. added, deleted
		16, 17	Figure 3.1, Figure 3.2; Part Number added, deleted
		24, 25	Table 5.4, Table 5.5; Conditions: VCC = 5.0 V at Topr = 25 °C deleted